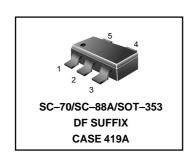
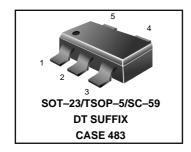
## 2-Input NAND Gate

### **MC74VHC1G00**

The MC74VHC1G00 is an advanced high speed CMOS 2-input NAND gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation. The internal circuit is composed of multiple stages, including a buffer output which provides high noise immunity and stable output. The MC74VHC1G00 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHC1G00 to be used to interface 5 V circuits to 3 V circuits.

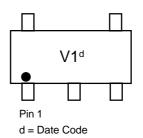
- High Speed:  $t_{PD} = 3.0 \text{ ns}$  (Typ) at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: I cc = 2 mA (Max) at T A = 25°C
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families

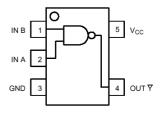




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#### **MARKING DIAGRAMS**





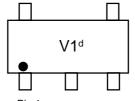


Figure 1. Pinout (Top View)

Pin 1

Figure 2. Logic Symbol

d = Date Code

#### **FUNCTION TABLE**

Inp	outs	Output
Α	В	Y
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

#### 2 IN A 3 **GND** 4 OUT $\overline{Y}$

**PIN ASSIGNMENT** 

IN B

 $V_{cc}$ 

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

#### MC74VHC1G00

#### **MAXIMUM RATINGS**

Symbol	Parameter		Value	Unit
V <sub>cc</sub>	DC Supply Voltage		- 0.5 to + 7.0	V
V <sub>IN</sub>	DC Input Voltage		$-0.5$ to V $_{\rm CC}$ + 0.5	V
V <sub>OUT</sub>	DC Output Voltage		$-0.5$ to V $_{\rm CC}$ + 0.5	V
Lik	DC Input Diode Current		± 20	mA
I ok	DC Output Diode Current		± 20	mA
I <sub>OUT</sub>	DC Output Sink Current		± 12.5	mA
I <sub>cc</sub>	DC Supply Current per Supply Pin		± 25	mA
T <sub>STG</sub>	Storage Temperature Range		- 65 to + 150	°C
Τ <sub>L</sub>	Lead Temperature, 1 mm from Cas	e for 10 Seconds	260	°C
Τ <sub>J</sub>	Junction Temperature Under Bias		+ 150	°C
$\theta$ JA	Thermal Resistance	SC-70/SC-88A (Note 1)	150	°C/W
		TSOP-5	200	
P <sub>D</sub>	Power Dissipation in Still Air at 85C	SC-70/SC-88A	150	mW
		TSOP-5	230	
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% – 35%	UL 94 V-0 (0.125 in)	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 2)	>2000	V
		Machine Model (Note 3)	> 200	
		Charged Device Model (Note 4)	N/A	
I LATCH-UP	Latch-Up Performance Above	V cc and Below GND at 85C (Note 5)	± 500	mA

Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

- $1.\ Measured\ with\ minimum\ pad\ spacing\ on\ an\ FR4\ board,\ using\ 10\ mm-by-1\ inch,\ 2-ounce\ copper\ trace\ with\ no\ air\ flow.$
- 2. Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit		
V <sub>CC</sub>	DC Supply Voltage	2.0	5.5	V		
V <sub>IN</sub>	DC Input Voltage	0.0	5.5	V		
V <sub>OUT</sub>	DC Output Voltage	0.0	V cc	V		
T <sub>A</sub>	Operating Temperature Range		<b>–</b> 55	+ 125	°C	
tr,tf	Input Rise and Fall Time	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	0	100	ns/V	
		$V_{CC} = 5.0 \pm 0.5 V$	0	20		

# DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

THE TO 0:170 BOND TAILORES								
Time,	Time,							
Hours	Years							
1,032,200	117.8							
419,300	47.9							
178,700	20.4							
79,600	9.4							
37,000	4.2							
17,800	2.0							
8,900	1.0							
	Time, Hours 1,032,200 419,300 178,700 79,600 37,000 17,800							

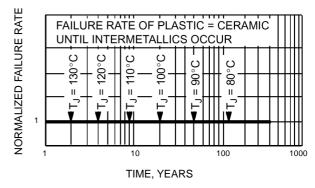


Figure 3. Failure Rate vs. Time Junction Temperature

#### MC74VHC1G00

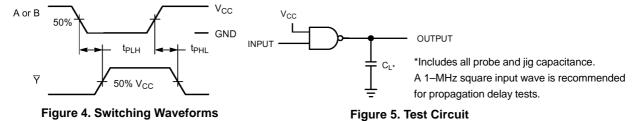
#### DC ELECTRICAL CHARACTERISTICS

			V cc	T <sub>A</sub> = <b>25</b> °C		T <sub>A</sub> ≤	<b>85</b> °C	<b>–55</b> °C t			
Symbol	Parameter	<b>Test Conditions</b>	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level		2.0	1.5			1.5		1.5		V
	Input Voltage		3.0	2.1			2.1		2.1		
			4.5	3.15			3.15		3.15		
			5.5	3.85			3.85		3.85		
V <sub>IL</sub>	Maximum Low-Level		2.0			0.5		0.5		0.5	V
	Input Voltage		3.0			0.9		0.9		0.9	
			4.5			1.35		1.35		1.35	
			5.5			1.65		1.65		1.65	
V <sub>OH</sub>	Minimum High-Level	$V_{IN} = V_{IH} \text{ or } V_{IL}$	2.0	1.9	2.0		1.9		1.9		V
	Output Voltage	$I_{OH} = -50 \mu A$	3.0	2.9	3.0		2.9		2.9		
	$V_{IN} = V_{IH} \text{ or } V_{IL}$		4.5	4.4	4.0		4.4		4.4		
		$V_{IN} = V_{IH} \text{ or } V_{IL}$									İ
		$I_{OH} = -4 \text{ mA}$	3.0	2.58			2.48		2.34		
		$I_{OH} = -8 \text{ mA}$	4.5	3.94			3.80		3.66		
V <sub>OL</sub>	Maximum Low-Level	$V_{IN} = V_{IH} \text{ or } V_{IL}$	2.0		0.0	0.1		0.1		0.1	V
	Output Voltage	$I_{OL} = 50 \mu A$	3.0		0.0	0.1		0.1		0.1	
	$V_{IN} = V_{IH} \text{ or } V_{IL}$		4.5		0.0	0.1		0.1		0.1	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$									İ
		$I_{OL} = 4 \text{ mA}$	3.0			0.36		0.44		0.52	
		$I_{OL} = 8 \text{ mA}$	4.5			0.36		0.44		0.52	
I <sub>IN</sub>	Maximum Input	V <sub>IN</sub> = 5.5 V or GND	0 to5.5			±0.1		±1.0		±1.0	μΑ
	Leakage Current										
I <sub>cc</sub>	Maximum Quiescent	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5			2.0		20		40	μΑ
	Supply Current										

AC ELECTRICAL CHARACTERISTICS C  $_{load}$  = 50 pF, Input t  $_{r}$  = t  $_{f}$  = 3.0 ns

				Т	T <sub>A</sub> = <b>25</b> °C		$T_A \leq 85^{\circ}C$ -5		-55°C <t<sub>A &lt;125°C</t<sub>		
Symbol	Parameter	<b>Test Conditions</b>		Min	Тур	Max	Min	Max	Min	Max	Unit
t PLH,	Maximum	$V_{CC} = 3.3 \pm 0.3 V$	C ∟= 15 pF		4.5	7.9		9.5		11.0	ns
t <sub>PHL</sub>	Propagation Delay,		C <sub>L</sub> = 50 pF		5.6	11.4		13.0		15.1	
	Input A or B to $\overline{Y}$										
		$V_{CC} = 5.0 \pm 0.5 V$	C <sub>L</sub> = 15 pF		3.0	5.5		6.5		8.0	
			C <sub>L</sub> = 50 pF		3.8	7.5		8.5		10.0	
C IN	Maximum Input				5.5	10		10		10	pF
	Capacitance										
				Турі	cal @ 2	25 <b>°C, V</b>	cc = <b>5.0</b>	) V		•	
C PD	Power Dissipation Capacitance (Note 6)					10				pF	

<sup>6.</sup> C  $_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I  $_{CC(OPR)} = C _{PD} \cdot V _{CC} \cdot f _{in} + I _{CC} \cdot C _{PD}$  is used to determine the noload dynamic power consumption; P  $_{D} = C _{PD} \cdot V _{CC}^2 \cdot f _{in} + I _{CC} \cdot V _{CC}$ .



### MC74VHC1G00

#### **DEVICE ORDERING INFORMATION**

		Device Nomenclature							
Device Order Number	Logic Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape and Reel Suffix	Package Type (Name/SOT#/ Common Name)	Tape and Reel Size	
MC74VHC1G00DFT	MC	74	VHC1G	00	DF	T1	SC-70/SC-88A/	178 mm (7 in)	
							SOT-353	3000 Unit	
MC74VHC1G00DFT2	MC	74	VHC1G	00	DF	T2	SC-70/SC-88A/	178 mm (7 in)	
							SOT-353	3000 Unit	
MC74VHC1G00DTT1	MC	74	VHC1G	00	DT	T1	SOT-23/TSOP-5/	178 mm (7 in)	
							SC-59	3000 Unit	